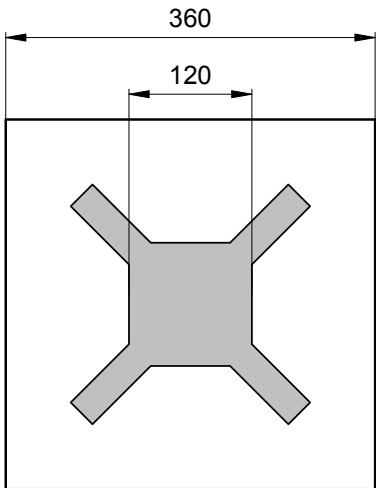


Radiation	Type	Technology	Electrodes
Infrared	DH	AlGaAs/GaAs	P (anode) up

 <p style="text-align: center;">LED-14</p>	typ. dimensions (μm)	
	<u>typ. thickness</u> 260 (± 20) μm	
	<u>anode</u> gold alloy, 1.5 μm	
	<u>cathode</u> gold alloy, 0.5 μm , dotted, 25% covered	

Optical and Electrical Characteristics

$T_{\text{amb}} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.2	1.4	V
Reverse voltage	$I_R = 100 \mu\text{A}$	V_R	5			V
Radiant power*	$I_F = 20 \text{ mA}$	Φ_e	1.2	1.7		mW
Radiant power*	$I_F = 50 \text{ mA}$	Φ_e	3.0	4.2		mW
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p	920	935	950	nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		50		nm
Switching time	$I_F = 20 \text{ mA}$	t_r, t_f		600		ns

*Measured on bare chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	$\Phi_e(\text{typ})$ [mW]	$V_F(\text{typ})$ [V]	Quantity
ELC-935-17				

Packing: Chips on adhesive film with wire-bond side on top